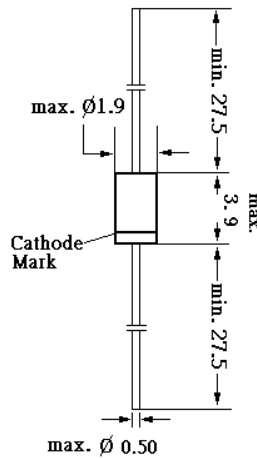


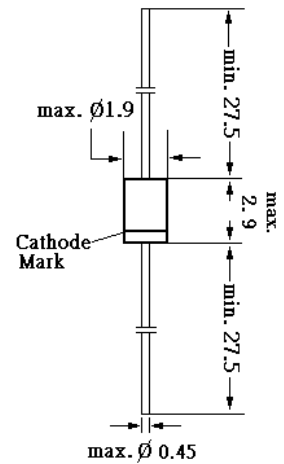
1N914...1N4454

SILICON EPITAXIAL PLANAR DIODES for general purpose and switching

The types 1N4149, 1N4447 and 1N4449 are also available in glass case DO-34.



Glass case JEDEC DO-35
Dimensions in mm



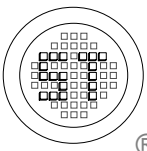
Glass case JEDEC DO-34
Dimensions in mm

Type	Peak reverse voltage	Max. aver. rectified current	Max. power dissip. at 25°C	Max. junction temperature	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
	V_{RM} V	I_{OM} mA	P_{tot} mW	T_j °C	V_F V	at I_F mA	I_n nA	at V_R V	t_{rr} ns	Conditions
1N914	100	75	500	200	1	10	25	20	Max.4	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4149 ¹⁾	100	150	500	200	1	10	25	20	Max.4	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4151	75	150	500	200	1	50	50	50	Max.2	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4152	40	150	400	175	0.55	0.1	50	30	Max.2	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4153	75	150	400	175	0.55	0.1	50	50	Max.2	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4154	35	150 ²⁾	500	200	1	30	100	25	Max.2	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4447 ¹⁾	100	150	500	200	1	20	25	20	Max.4	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4449 ¹⁾	100	150	500	200	1	30	25	20	Max.4	$I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\ \Omega$, to $I_R=1\text{mA}$
1N4450	40	150	400	175	0.54	0.5	50	30	Max.4	$I_F=I_R=10\text{mA}$, to $I_R=1\text{mA}$
1N4451	40	150	400	175	0.5	0.1	50	30	Max.10	$I_F=I_R=10\text{mA}$, to $I_R=1\text{mA}$
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1	10	100	50	Max.4	$I_F=I_R=10\text{mA}$, to $I_R=1\text{mA}$

1). These diodes are also available in glass case DO-34.

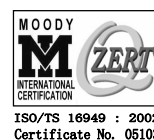
2). Valid provided that leads at a distance of 8mm from case are kept at ambient temperature.

Parameters for diodes in case DO-34: $P_{tot} = 300\text{mW}$ $T_s = -65\text{ to }+175^\circ\text{C}$
 $T_j = 175^\circ\text{C}$ $R_{thA} = \leq 0.4\text{ K/mW}$



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 31/12/2002